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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	9 6	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	26	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	27	mJ	$I_D=2.5\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche energy, repetitive	E_{AR}	-	-	0.14	mJ	$I_D=2.5\text{A}$; $V_{DD}=50\text{V}$; see table 10
Avalanche current, single pulse	I_{AS}	-	-	2.5	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	80	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	41	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current	I_S	-	-	9	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	26	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 9\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di/dt	-	-	900	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq 9\text{A}$, $T_j=25^\circ\text{C}$ see table 8
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$. Maximum Duty Cycle $D = 0.50$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_θ

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	3.04	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	-	°C/W	-
Soldering temperature, wavesoldering only allowed at leads	T_{sld}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$, $I_D=0.14mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600V$, $V_{GS}=0V$, $T_j=25^\circ\text{C}$ $V_{DS}=600V$, $V_{GS}=0V$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	1000	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.300 0.702	0.360 -	Ω	$V_{GS}=10V$, $I_D=2.7A$, $T_j=25^\circ\text{C}$ $V_{GS}=10V$, $I_D=2.7A$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	6.2	-	Ω	$f=1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	555	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Output capacitance	C_{oss}	-	10	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	20	-	pF	$V_{GS}=0V$, $V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	214	-	pF	$I_D=\text{constant}$, $V_{GS}=0V$, $V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	8	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=2.7A$, $R_G=10.0\Omega$; see table 9
Rise time	t_r	-	7	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=2.7A$, $R_G=10.0\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	42	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=2.7A$, $R_G=10.0\Omega$; see table 9
Fall time	t_f	-	10	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=2.7A$, $R_G=10.0\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	3	-	nC	$V_{DD}=400V$, $I_D=2.7A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	4	-	nC	$V_{DD}=400V$, $I_D=2.7A$, $V_{GS}=0$ to $10V$
Gate charge total	Q_g	-	13	-	nC	$V_{DD}=400V$, $I_D=2.7A$, $V_{GS}=0$ to $10V$
Gate plateau voltage	$V_{plateau}$	-	5.2	-	V	$V_{DD}=400V$, $I_D=2.7A$, $V_{GS}=0$ to $10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=2.7A$, $T_J=25^{\circ}C$
Reverse recovery time	t_{rr}	-	145	-	ns	$V_R=400V$, $I_F=1A$, $di_F/dt=100A/\mu s$; see table 8
Reverse recovery charge	Q_{rr}	-	0.74	-	μC	$V_R=400V$, $I_F=1A$, $di_F/dt=100A/\mu s$; see table 8
Peak reverse recovery current	I_{rrm}	-	11	-	A	$V_R=400V$, $I_F=1A$, $di_F/dt=100A/\mu s$; see table 8

4 Electrical characteristics diagrams

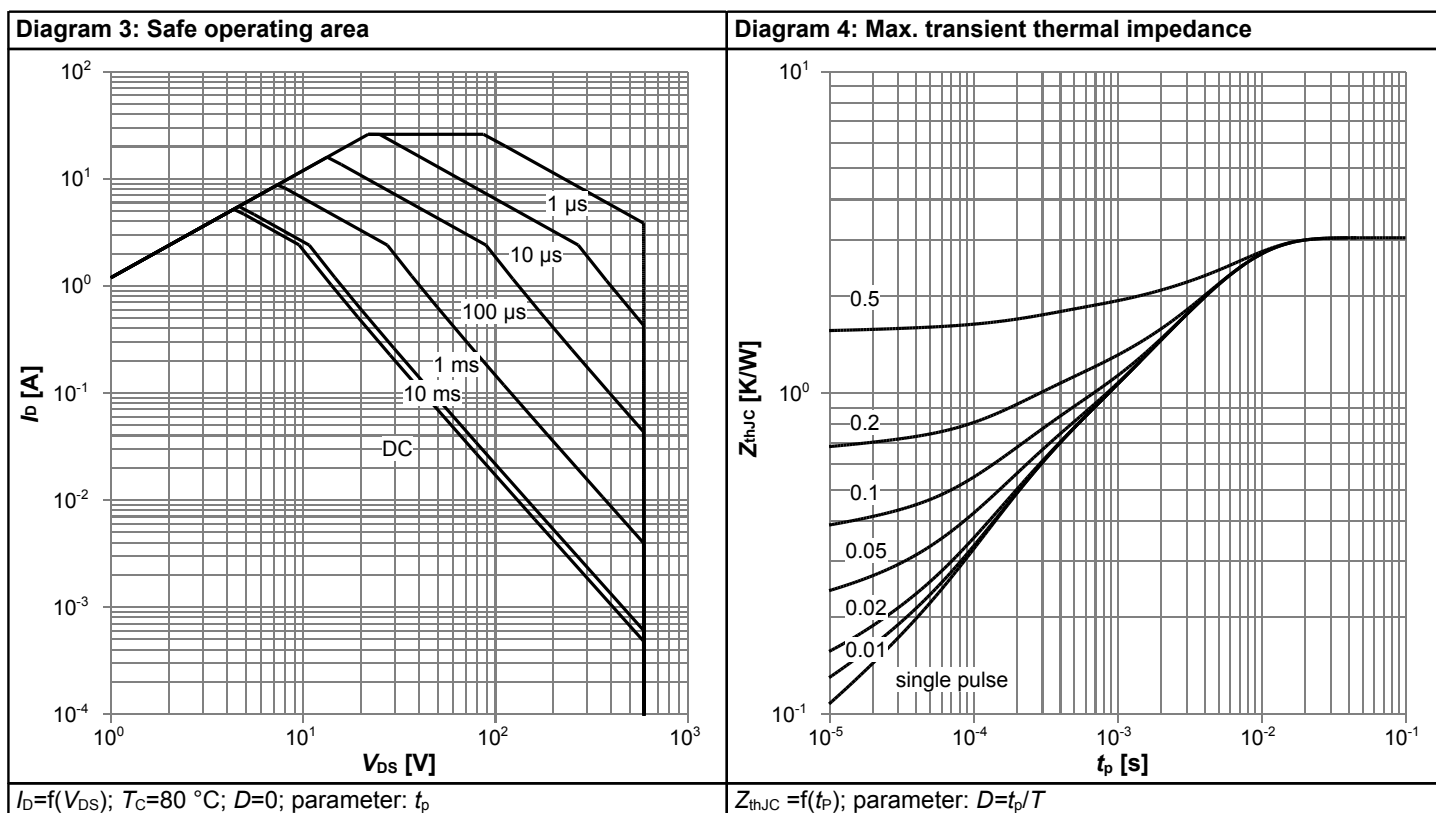
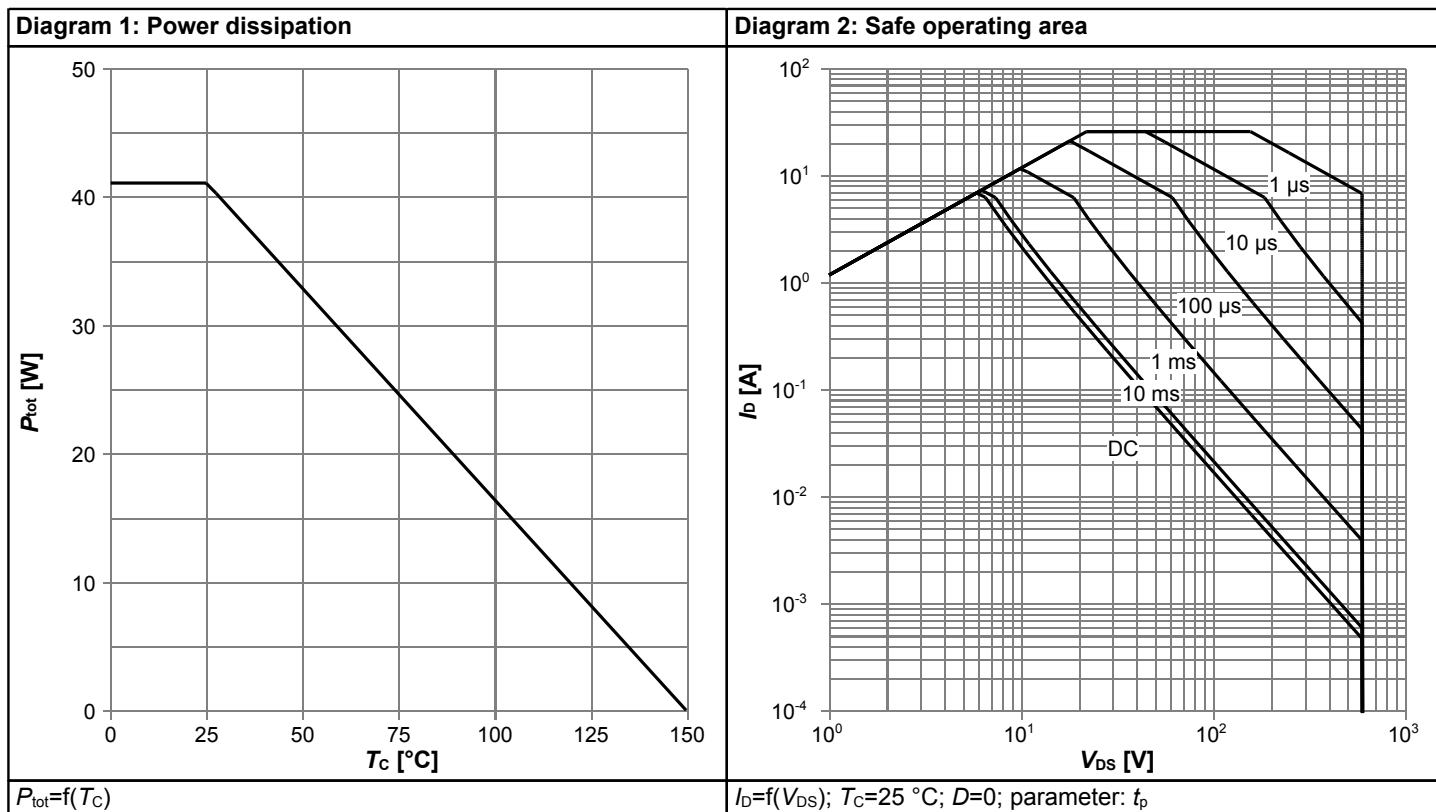
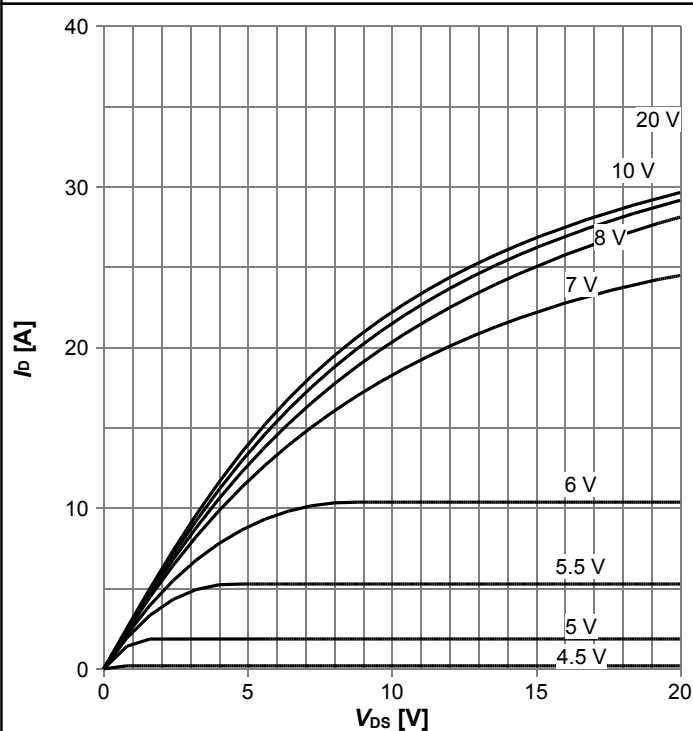
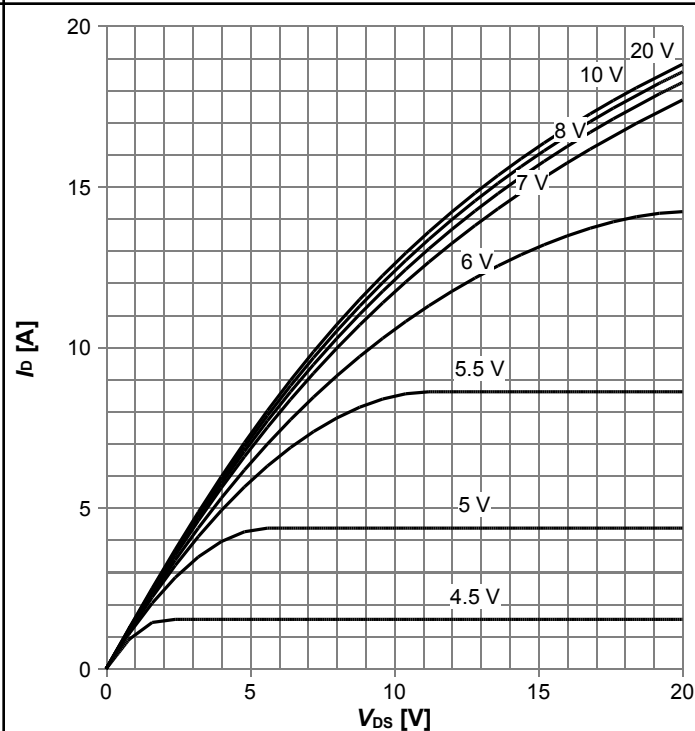


Diagram 5: Typ. output characteristics



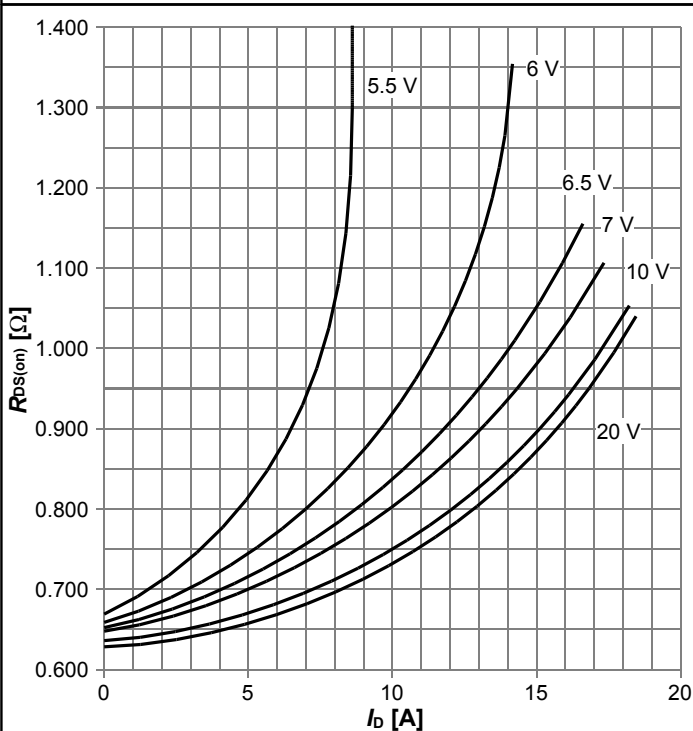
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics



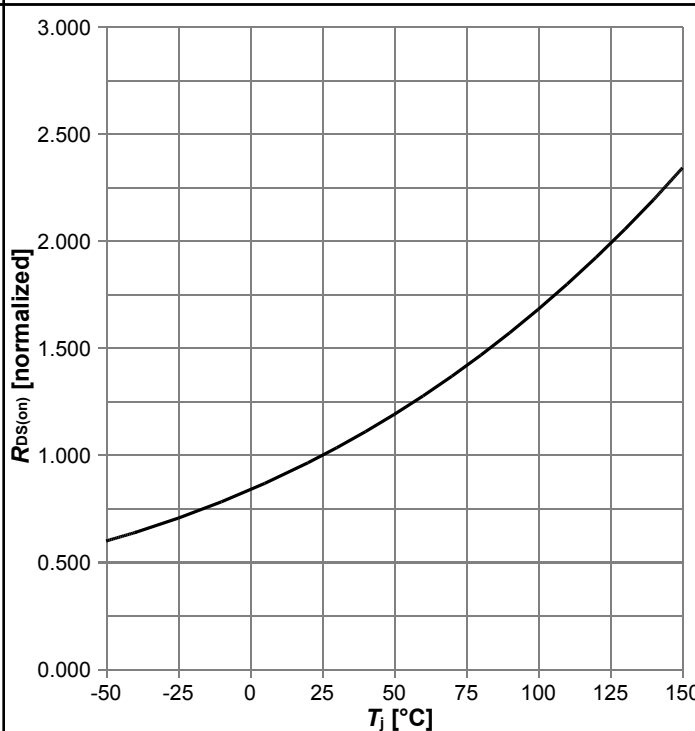
$I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



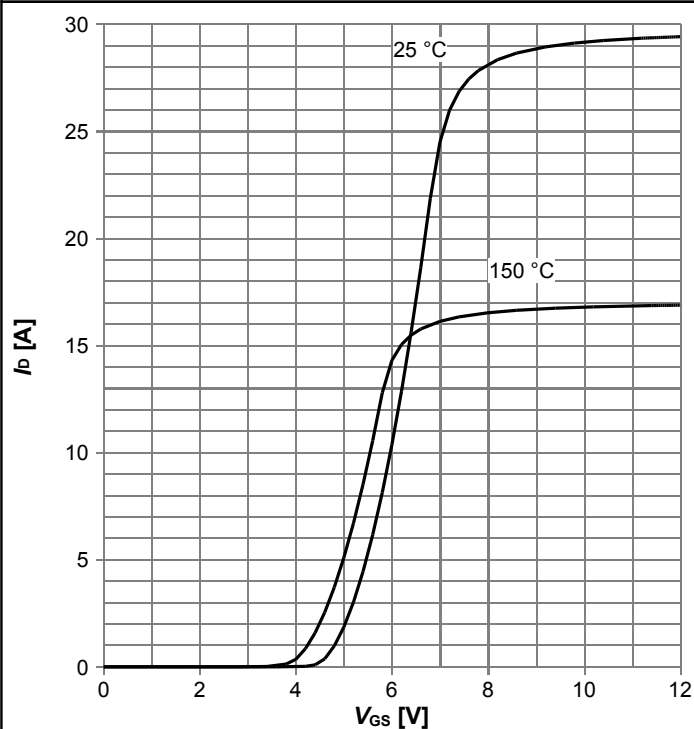
$R_{DS(on)} = f(I_D)$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



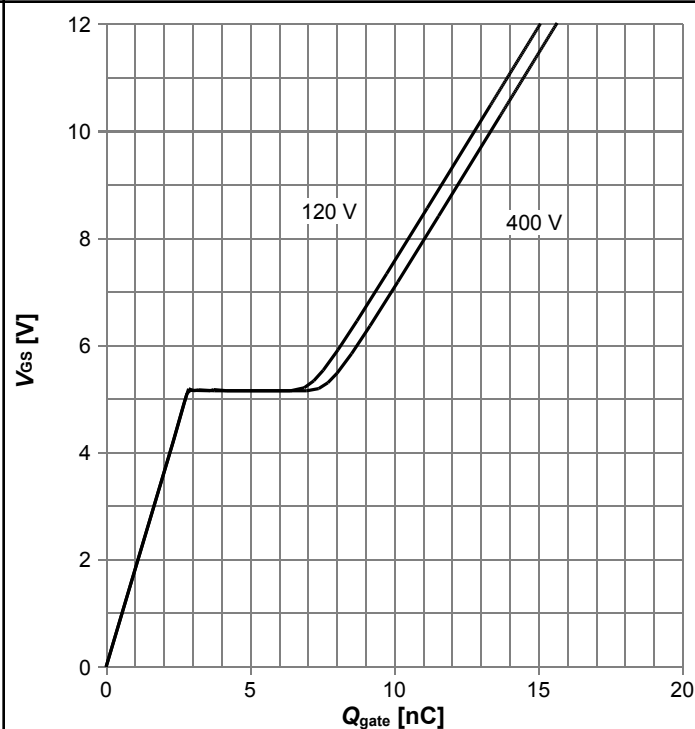
$R_{DS(on)} = f(T_j)$; $I_D = 2.7\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 9: Typ. transfer characteristics



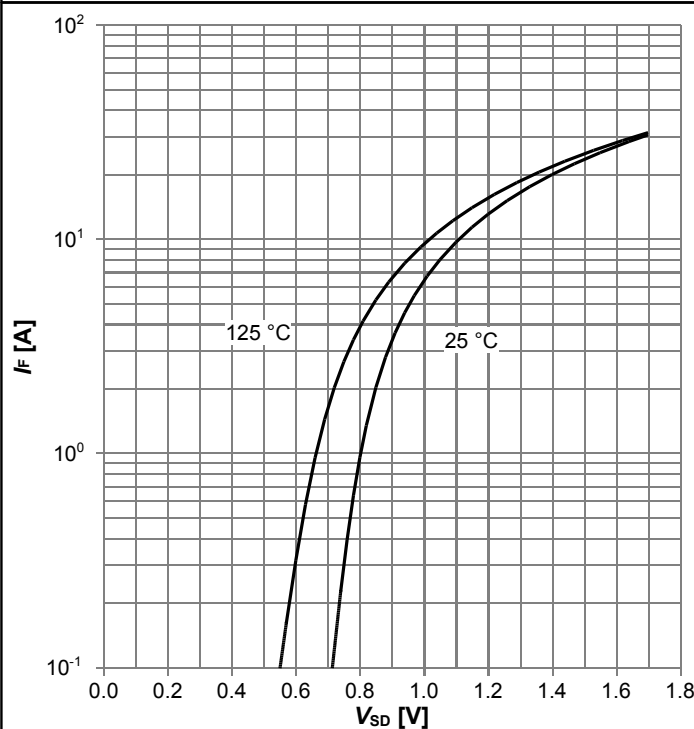
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 10: Typ. gate charge



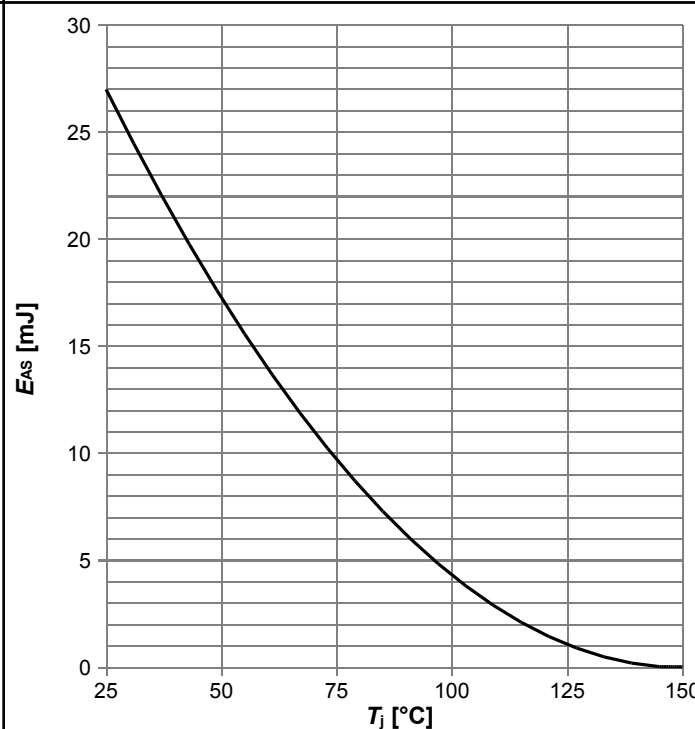
$V_{GS} = f(Q_{gate})$; $I_D = 2.7$ A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



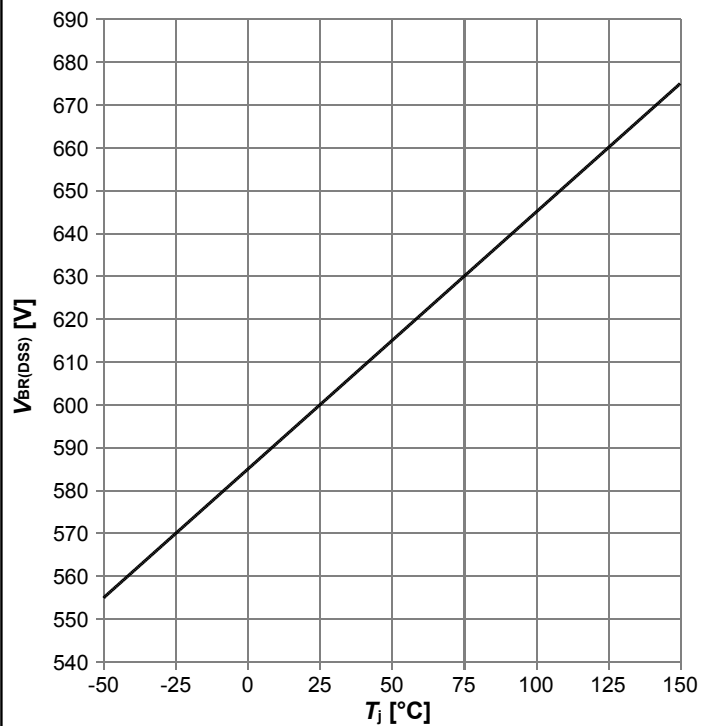
$I_F = f(V_{SD})$; parameter: T_j

Diagram 12: Avalanche energy



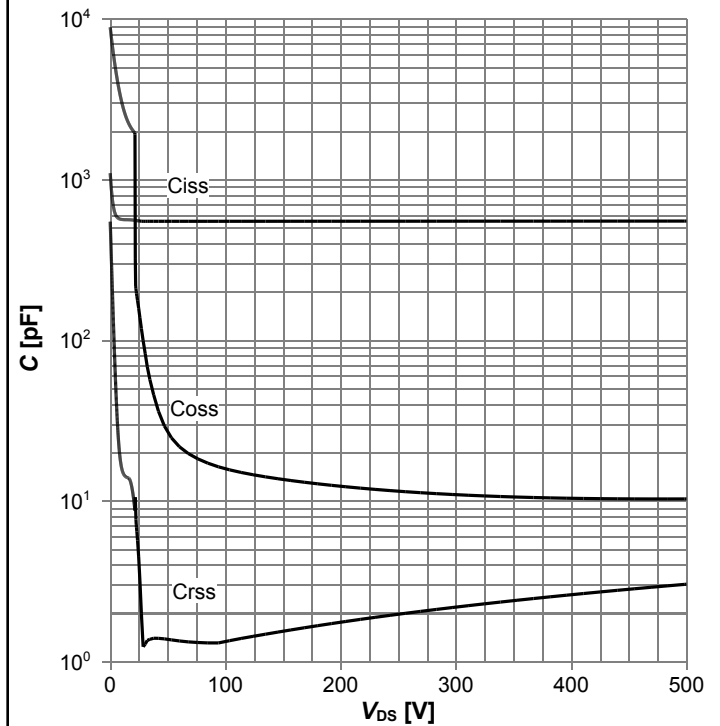
$E_{AS} = f(T_j)$; $I_D = 2.5$ A; $V_{DD} = 50$ V

Diagram 13: Drain-source breakdown voltage



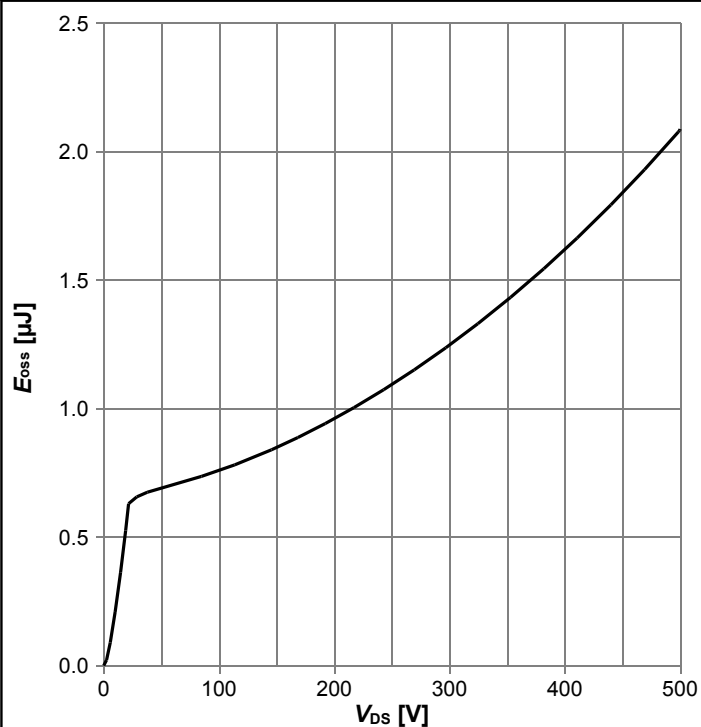
$V_{BR(DSS)} = f(T_J); I_D = 1 \text{ mA}$

Diagram 14: Typ. capacitances



$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss} = f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

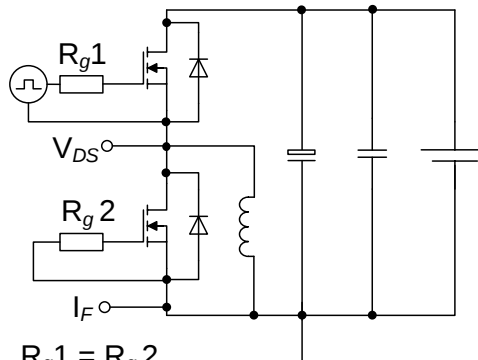
Test circuit for diode characteristics	Diode recovery waveform
 $R_{g1} = R_{g2}$	

Table 9 Switching times

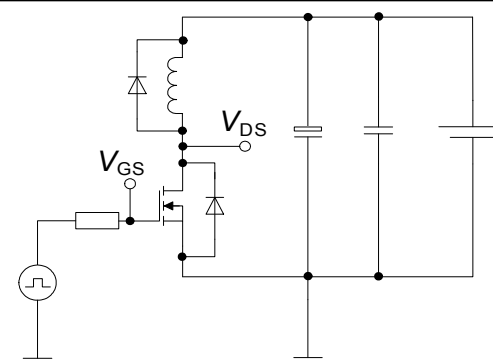
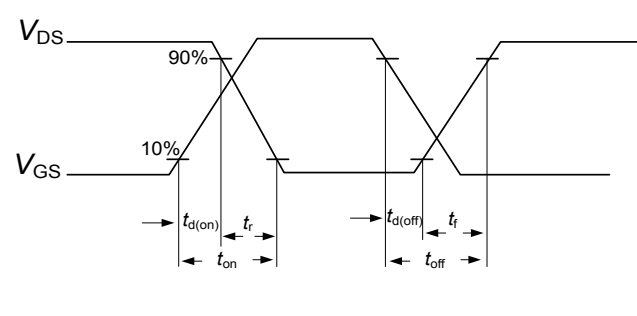
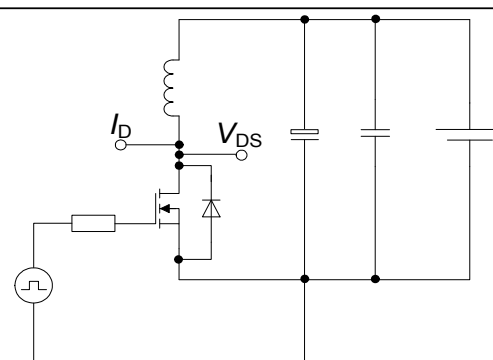
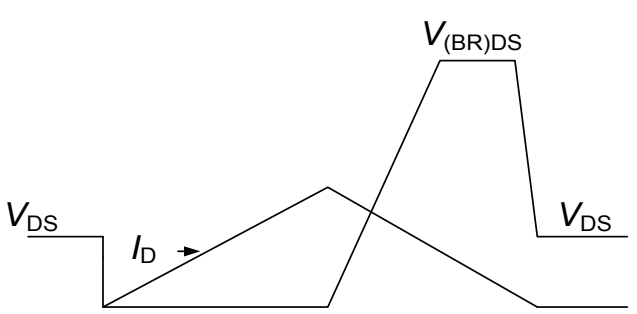
Switching times test circuit for inductive load	Switching times waveform
	

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

6 Package Outlines

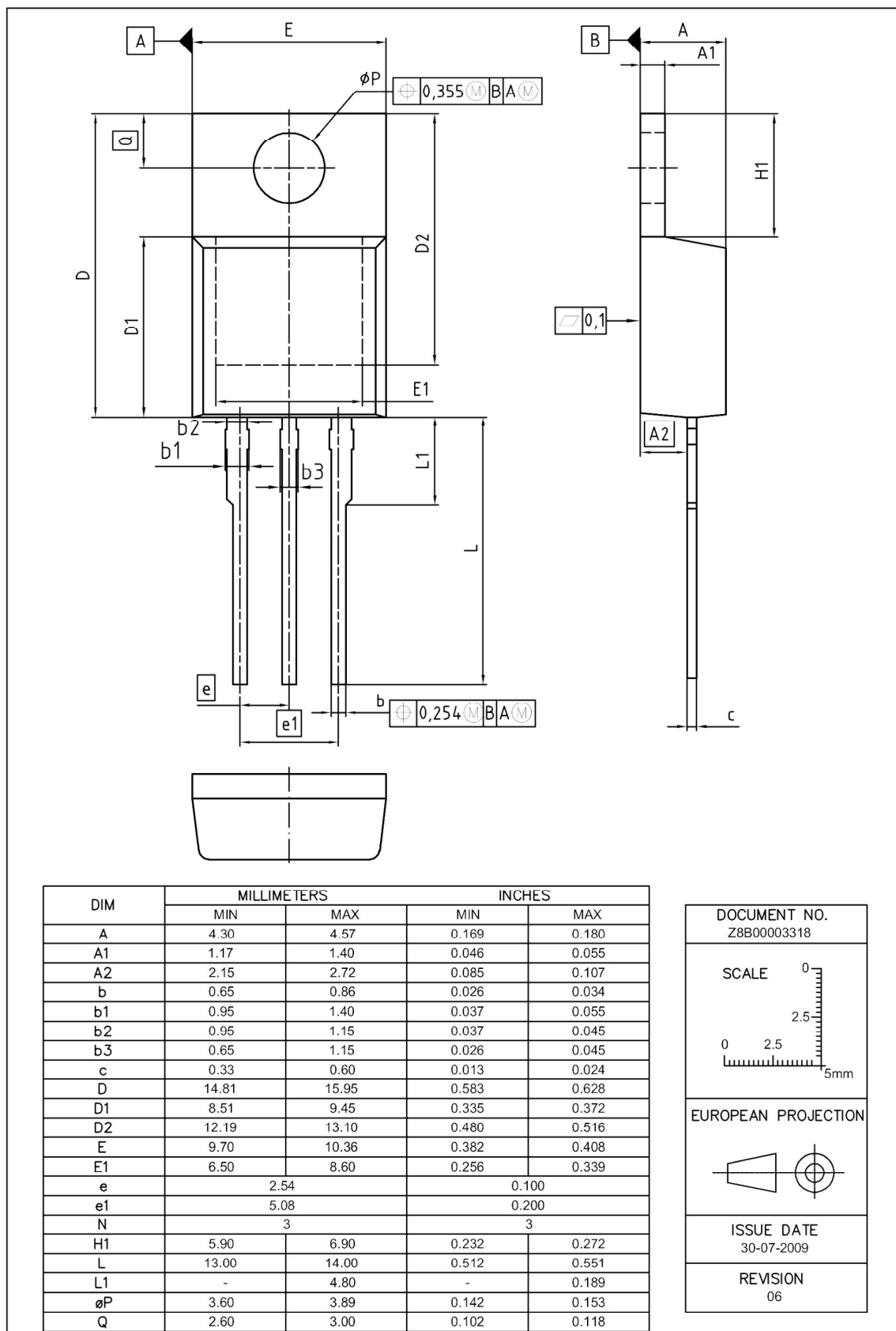


Figure 1 Outline PG-TO 220-3, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS P7 Webpage: www.infineon.com
- IFX CoolMOS P7 application note: www.infineon.com
- IFX CoolMOS P7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPP60R360P7

Revision: 2018-06-07, Rev. 2.3

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2017-02-03	Release of final version
2.1	2017-02-17	Modified Safe Operating Area diagrams on page 7
2.2	2017-03-02	updated y-axis label diagram 8
2.3	2018-06-07	Updated Co(er); Co(tr); Eoss; diagram scalings; Nomenclature of product qualification grade was changed, updated RDson typ at 25°C and 150°C

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